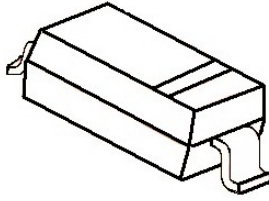


BZT52B Series

SOD-123 贴片塑封稳压二极管
SOD-123
SOD-123 Plastic-Encapsulate Zener Diode

特征 Features

- 齐纳击穿阻抗低; Low Zener Impedance
- 最大功率耗散 500mW; Power Dissipation of 500mW
- 高稳定性和可靠性。High Stability and High Reliability

机械数据 Mechanical Data

- 封装: SOD-123 封装 SOD-123 Small Outline Plastic Package
- 极性: 色环端为负极 Polarity: Color band denotes cathode end
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
功率消耗 Power Dissipation	Pd	500 ₁₎	mW
正向压降 Forward Voltage @IF=10mA	Vf	0.9 ₂₎	V
热阻 Thermal Resistance, Junction to Ambient Air	R _{θJA}	357	°C/W
工作结温 Junction/Operating Temperature	Tj	150	°C
存储温度 Storage temperature range	Ts	-65-+150	°C

 1) Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm²

2) Short duration test pulse used to minimize self-heating effect

3) f=1KHZ

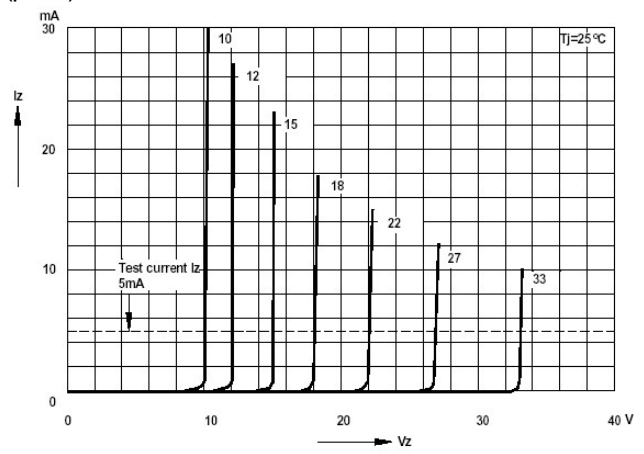
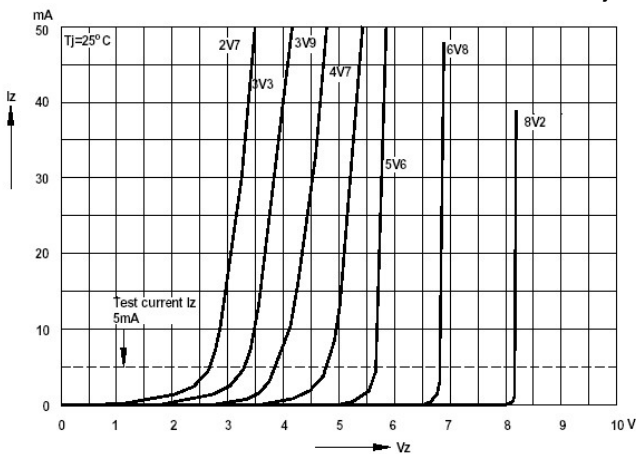
电特性 (TA = 25°C 除非另有规定) **Electrical Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified).

Device	Marking	Zener Voltage Range				Maximum Zener Impedance			Maximum Reverse Current		Typical Temperature coefficient @ IZTC=mV/°C		Test Current IZTC
		Vz@Izt			Izt	Zzt @Izt	Zzk @Izk	Izk	IR	VR	Min	Max	
		Nom(V)	Min(V)	Max(V)									
BZT52B2V4	2WX	2.4	2.35	2.45	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52B2V7	2W1	2.7	2.65	2.75	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52B3V0	2W2	3.0	2.94	3.06	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52B3V3	2W3	3.3	3.23	3.37	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52B3V6	2W4	3.6	3.53	3.67	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52B3V9	2W5	3.9	3.82	3.98	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52B4V3	2W6	4.3	4.21	4.39	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52B4V7	2W7	4.7	4.61	4.79	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52B5V1	2W8	5.1	5.00	5.20	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52B5V6	2W9	5.6	5.49	5.71	5	40	400	1.0	1	2.0	-2.0	2.5	5
BZT52B6V2	2WA	6.2	6.08	6.32	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52B6V8	2WB	6.8	6.66	6.94	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52B7V5	2WC	7.5	7.35	7.65	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52B8V2	2WD	8.2	8.04	8.36	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52B9V1	2WE	9.1	8.92	9.28	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52B10	2WF	10	9.80	10.20	5	20	150	1.0	0.2	7.0	4.5	8.0	5
BZT52B11	2WG	11	10.78	11.22	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52B12	2WH	12	11.76	12.24	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52B13	2WI	13	12.74	13.26	5	30	170	1.0	0.1	8.0	7.0	11.0	5

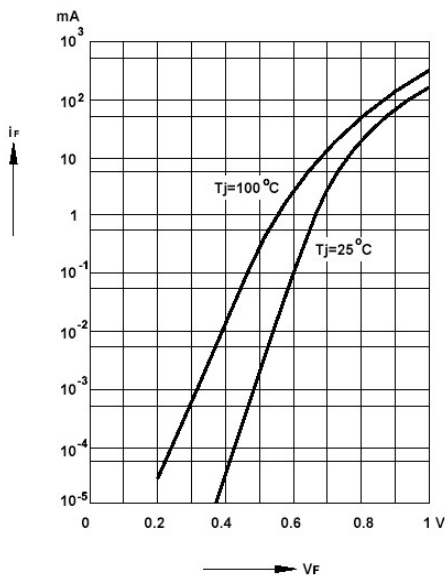
BZT52B Series

Device	Marking	Zener Voltage Range				Maximum Zener Impedance			Maximum Reverse Current		Typical Temperature coefficient @ IZTC=mV/°C		Test Current IZTC
		Vz@Izt			Izt	Zzt @Izt	Zzk @Izk	Izk	IR	VR	Min	Max	
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	uA	V			
BZT52B15	2WJ	15	14.70	15.30	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52B16	2WK	16	15.68	16.32	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52B18	2WL	18	17.64	18.36	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52B20	2WM	20	19.60	20.40	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52B22	2WN	22	21.56	22.44	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52B24	2WO	24	23.52	24.48	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52B27	2WP	27	26.46	27.54	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52B30	2WQ	30	29.40	30.60	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52B33	2WR	33	32.34	33.66	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52B36	2WS	36	35.28	36.72	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52B39	2WT	39	38.22	39.78	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52B43	2WU	43	41.16	43.84	2	100	700	1.0	0.1	32.0	10.0	12.0	5
BZT52B47	2WV	47	46.06	47.94	2	100	750	1.0	0.1	35.0	10.0	12.0	5
BZT52B51	2WW	51	49.98	52.02	2	100	750	1.0	0.1	38.0	10.0	12.0	5

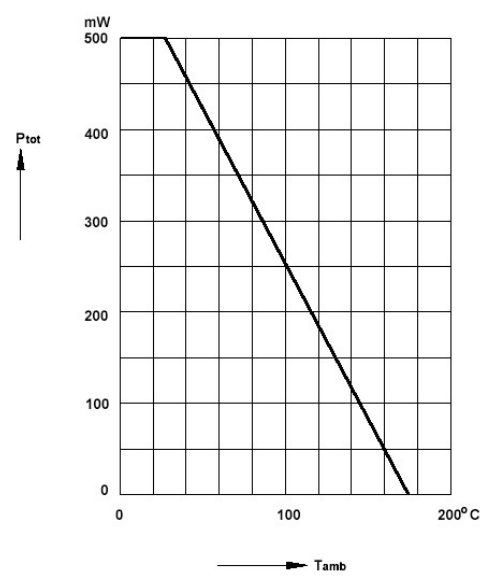
Breakdown characteristics
at Tj=constant (pulsed)



Forward characteristics

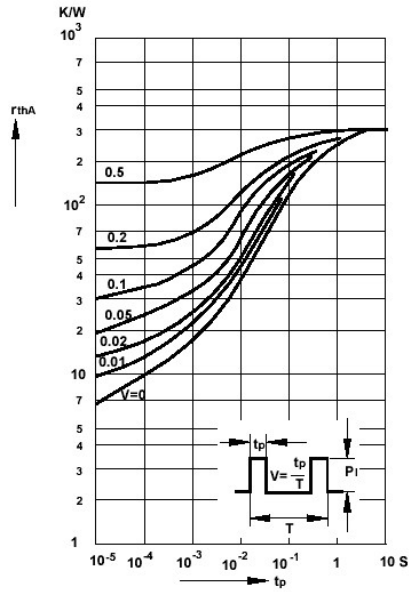


Admissible power dissipation versus ambient temperature

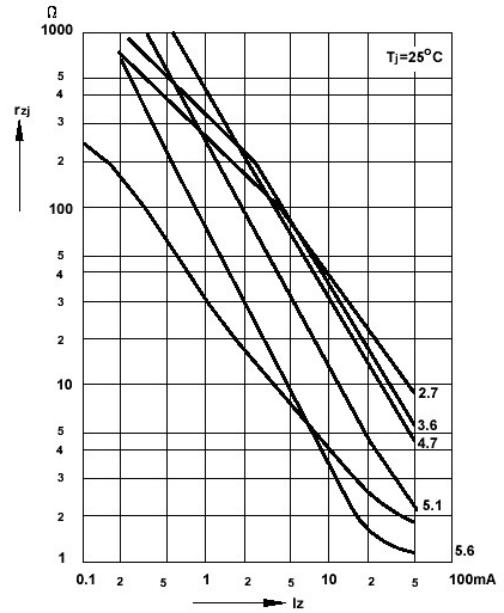


BZT52B Series

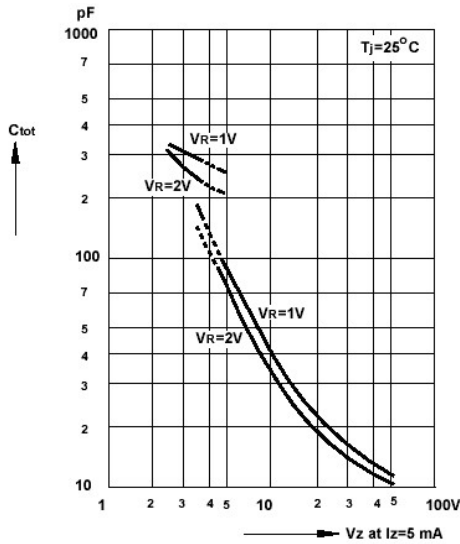
Pulse thermal resistance versus pulse duration



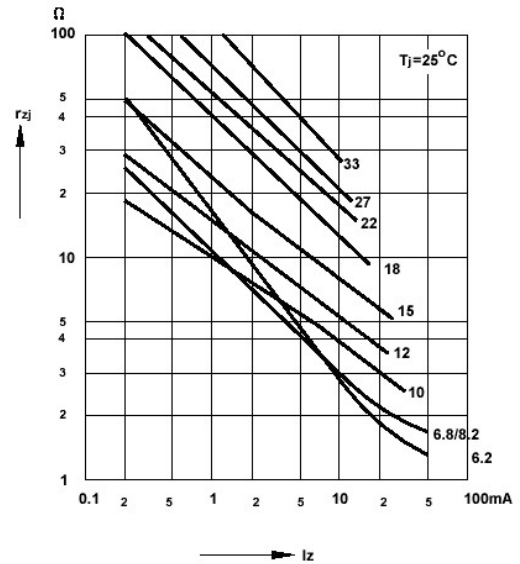
Dynamic resistance versus Zener current



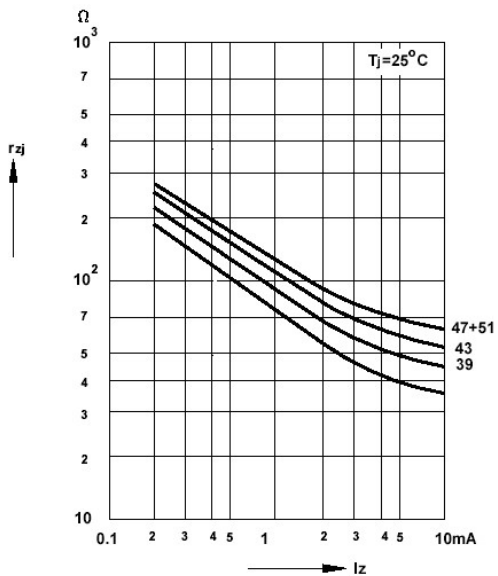
Capacitance versus Zener voltage



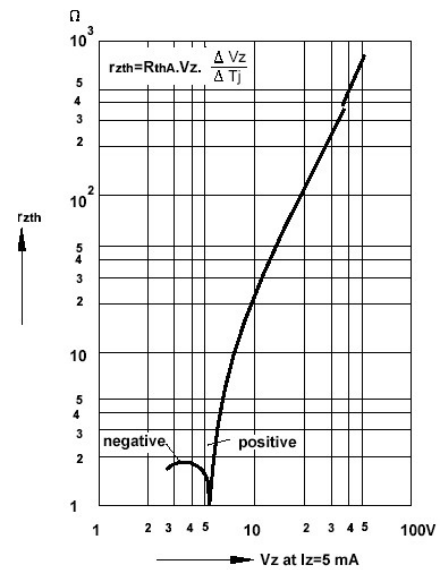
Dynamic resistance versus Zener current



Dynamic resistance versus Zener current

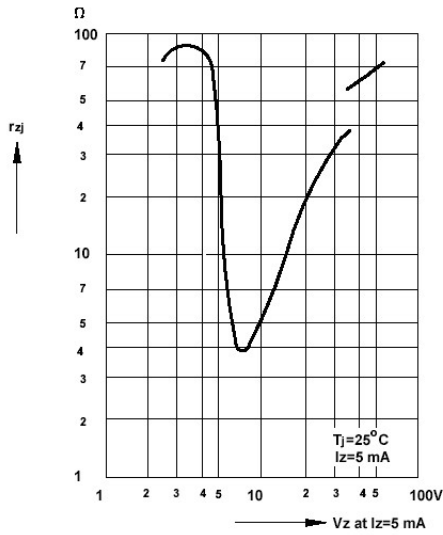


Thermal differential resistance versus Zener voltage

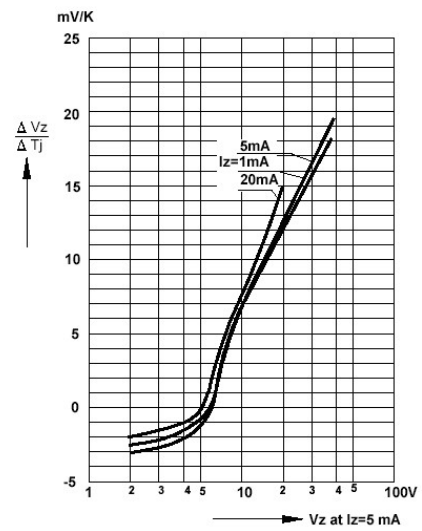


BZT52B Series

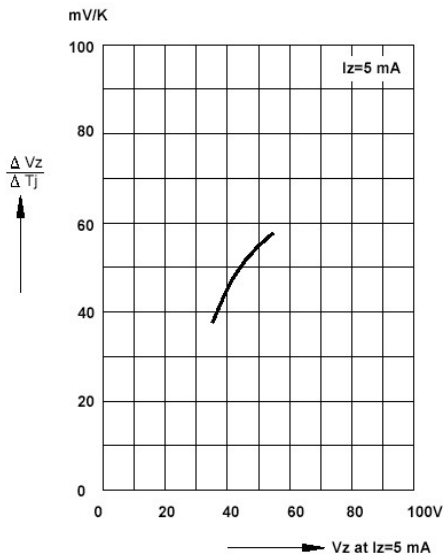
Dynamic resistance versus Zener voltage



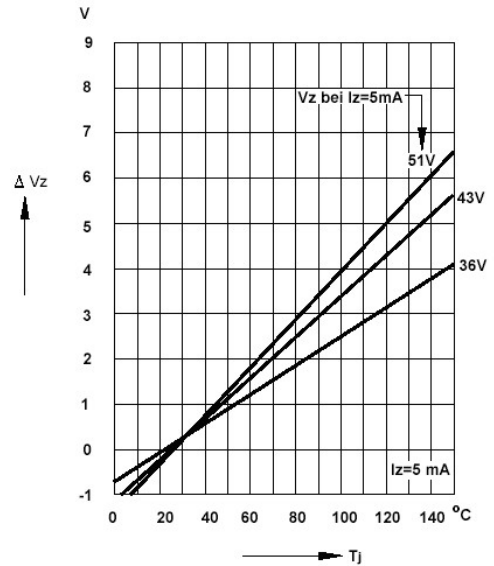
Temperature dependence of Zener voltage versus Zener voltage



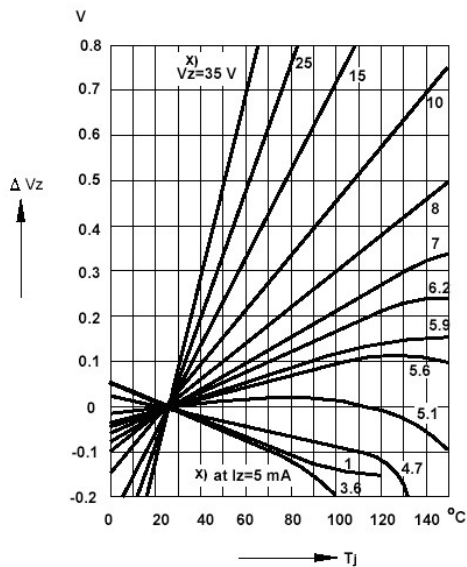
Temperature dependence of Zener voltage versus Zener voltage



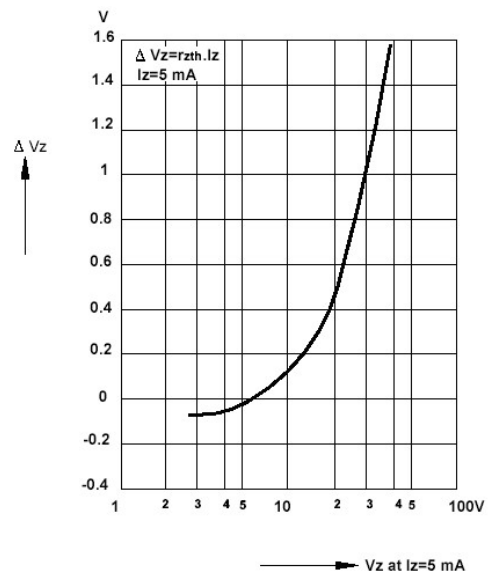
Change of Zener voltage versus junction temperature



Change of Zener voltage versus junction temperature

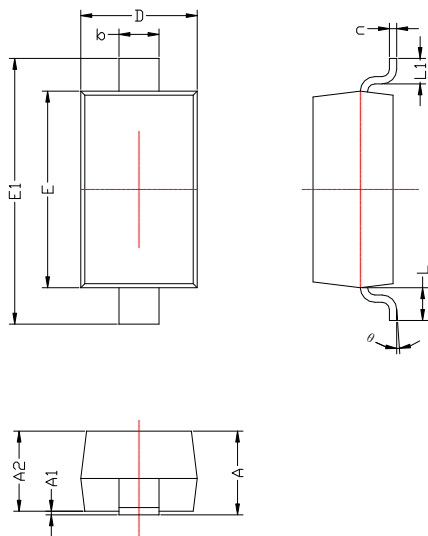


Change of Zener voltage from turn-on up to the point of thermal equilibrium versus Zener voltage



BZT52B Series

SOD-123 PACKAGE OUTLINE Plastic surface mounted package

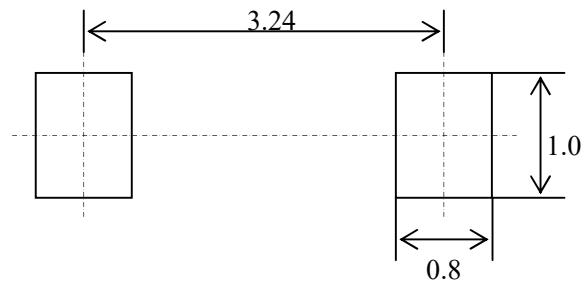


SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.450	0.650
c	0.080	0.150
D	1.500	1.700
E	2.600	2.800
E1	3.550	3.850
L	0.500REF	
L1	0.250	0.450
θ	0°	8°

焊盘设计参考

Precautions: PCB Design

Recommended land dimensions for SOD-123 diode. Electrode patterns for PCBs



中心距: 3.24
 脚宽: 0.55
 焊盘宽: 1.00
 脚长: 0.50
 焊盘长: 0.80

技术要求:

- 1, 塑封体尺寸: 2.70 X 1.60
- 2, 未注公差为: ± 0.05
- 3, 所有单位: mm